ABSTRACT OF THE DISCLOSURE

CLEANING LIQIUD FOR LITHOGRAPHY AND METHOD OF CLEANING THEREWITH

A cleaning liquid for lithography that exhibits equally excellent cleaning performance for resists of a wide variety of compositions, such as various resists for i-line, KrF and ArF, silicic resist and chemical amplification type positive resist, and that excels in post-treatment dryability, being free from any deterioration of resist performance by cleaning. There is provided a cleaning liquid for lithography, comprising at least one member (A) selected from among lower alkyl esters of acetic acid and propionic acid and at least one member (B) selected from among ketones having 5 to 7 carbon atoms per molecule in a mass ratio of (A):(B) of 4:6 to 7:3.